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Highlights

- $Ge_{20}Te_{80-x}Sn_x$ ($0 \leq x \leq 4$) glasses are synthesized through melt quenching technique.
- DSC thermograms obtained under non-isothermal conditions are analyzed and discussed.
- Various thermal parameters are calculated based on the variation of Sn content.
- Thermal stability and glass forming ability decrease with increase in Sn content.
- Easy devitrifiability of the glasses is useful for phase-change memory applications.

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